5 é

SOT-23 .> / / xJ´ PNP ƒ â ’ož Silicon PNP Digital Transistor in a SOT-23 Plastic Package.

¤ ª

Ä x ž å Š k • ¿ è — ‹ k × 5 « ^ y ò - v i k —)í D }ož

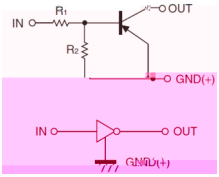
With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process,HF Product.

Đ ÷

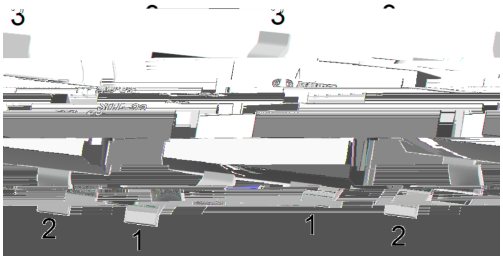
9 • ¼0• µ è Y C Ü è ož

Switching applications, interface circuit and driver circuit applications.

Ã W] Ô ·



• Û - æ



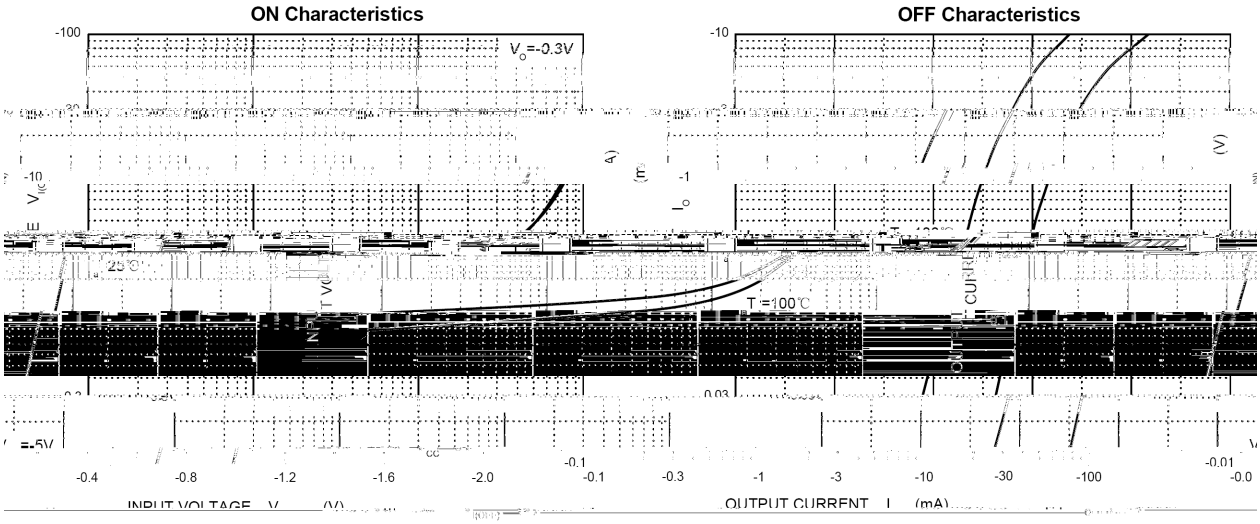
PIN1 y IN PIN 2 y GND PIN 3 y OUT

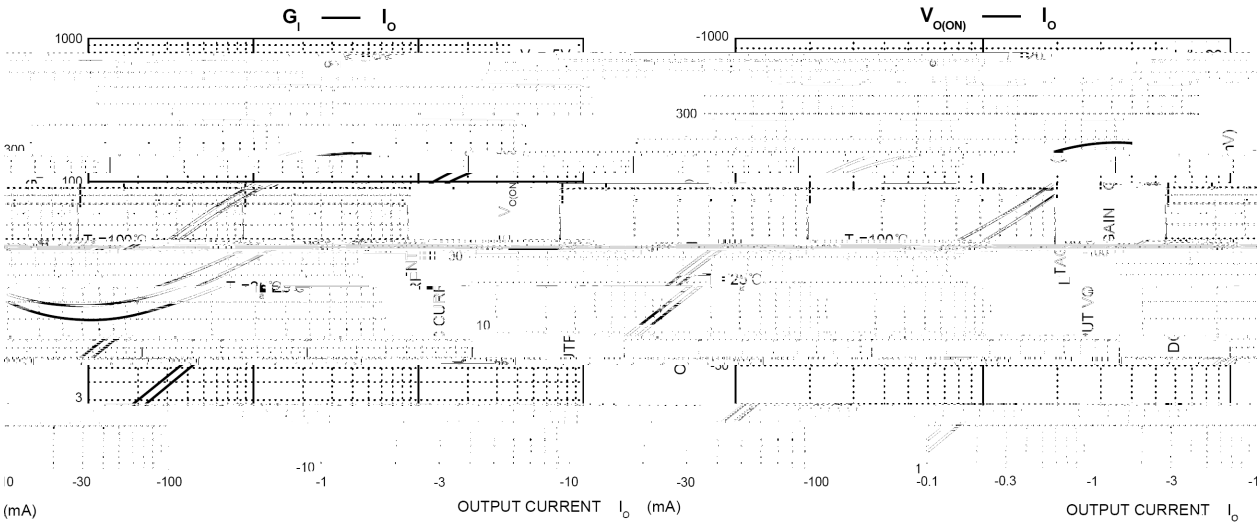
Z Ü B , M V

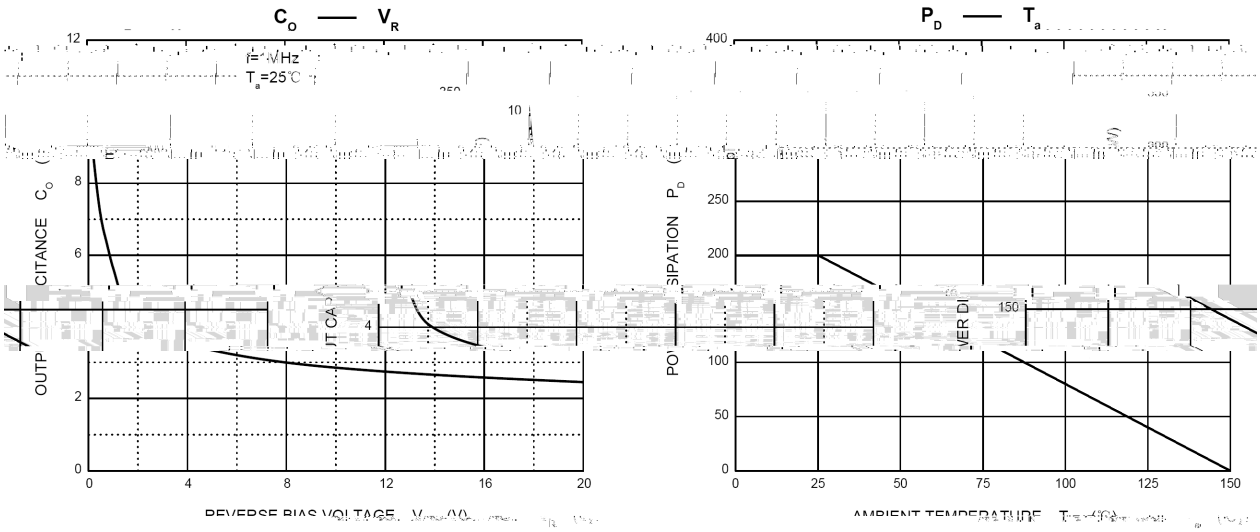
Marking	H14

@ *f* Parameter	… Z Symbol	*f* › Rating	% y Unit
Output Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	10	V
		-40	V
Output Current	I_O	-50	mA
Peak Collector Current	I_{CM}	-100	mA
Power Dissipation	P_D	200	mW
Junction Temperature	T_j	-55 150	

Ô ? d • Ž ¢


ON Characteristics
OFF Characteristics
V_o=-0.3V
25℃
T =100℃
INPUT VOLTAGE V (V)
OUTPUT CURRENT I (mA)

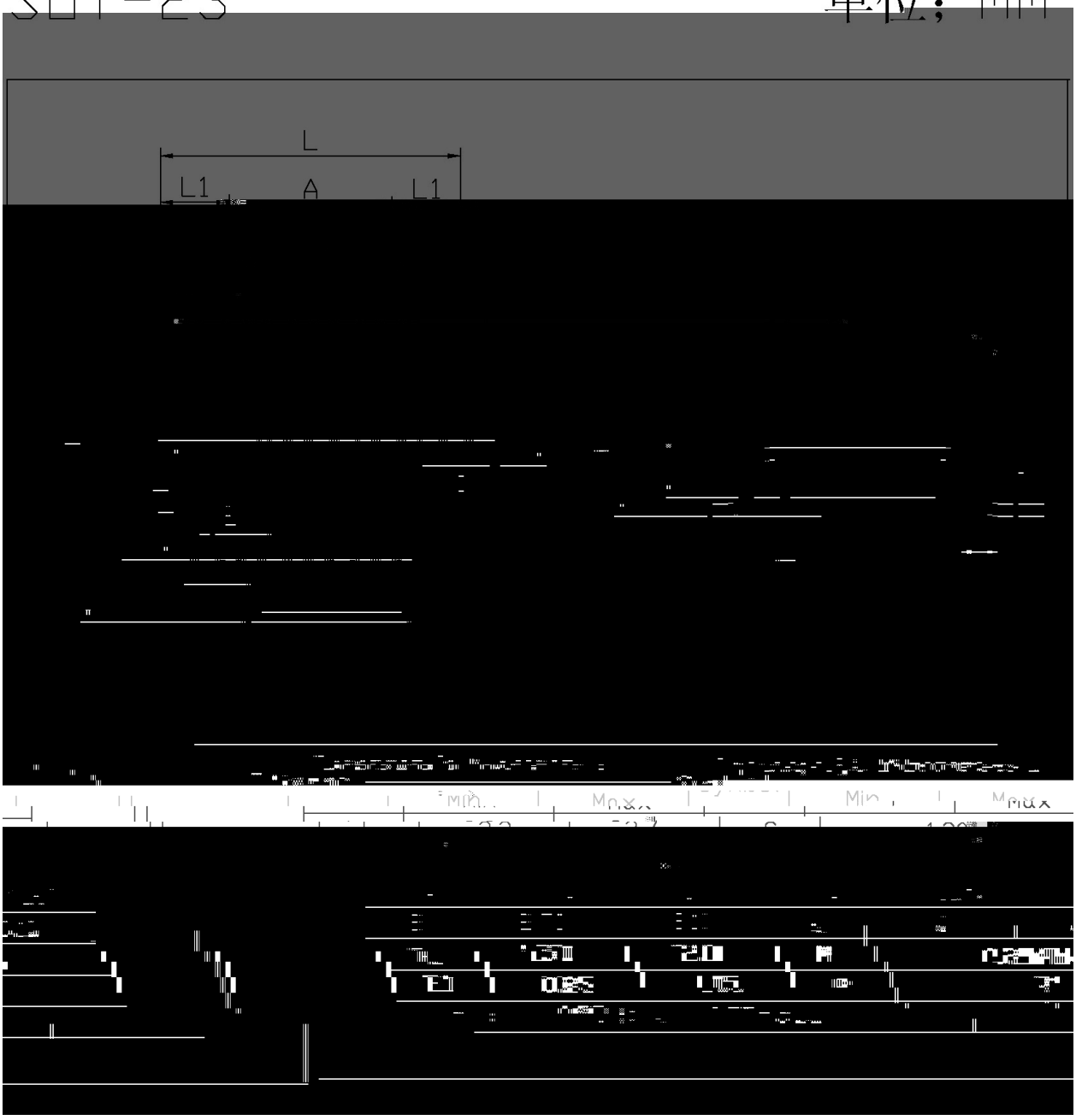

G_I — I_O
$V_{O(ON)}$ — I_O
OUTPUT CURRENT I_O (mA)
OUTPUT CURRENT I_O


C_O — V_R
P_D — T_a
f= MHz
T_a=25℃
REVERSE BIAS VOLTAGE V (V)
AMBIENT TEMPERATURE T (℃)

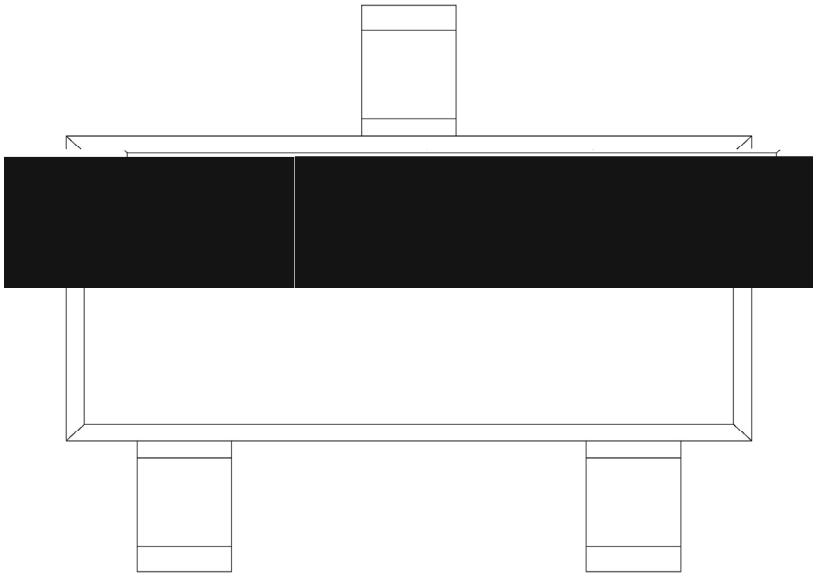
Ø ¤ =) ¢

SOT-23

单位：mm



, M y ƒ

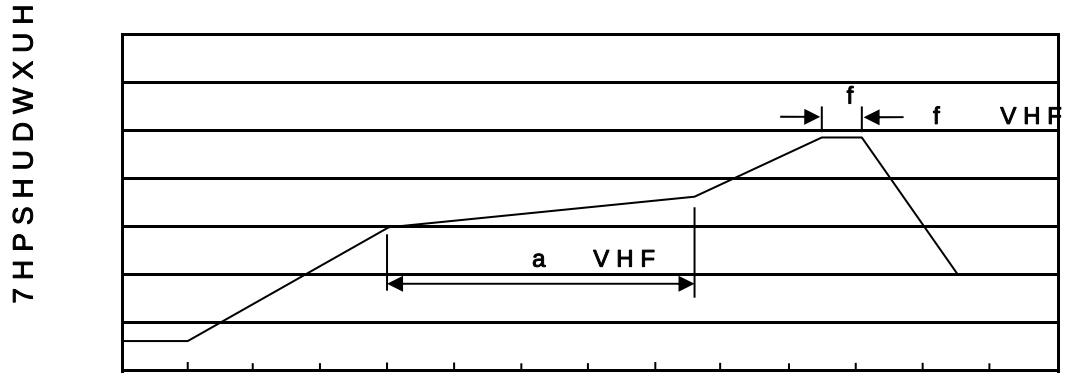


ª ¢ y

. y ¸ [W A

14

š WD t … • Ž ¢ x / :K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6



7 L P H V H F

ª ¢ y

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »]

“ † y 260 r5 - ž • y 10 r1 sec. Temp.:260±5 Time:10±1 sec

G P á

2 & x / REEL

Package Type 7>û ˜ E	Units ;>û ¦H					Dimension ;>û p . (unit Æmm³)		
	Units/Reel / --	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box×	Outer Box1ç
SOT-23	3,000	10	30,000	6	180,000	7 T×8	180×120×180	390×385×205

„ Ð y ƒ